



## 40 Mils, 200 Volt, 1 Amp

## **Data Sheet**

## Features

M Т ED

Oxide Passivated Junction Low Forward Voltage 150 ° C Junction Operating Low Reverse Leakage Supplied as Wafers Platinum Barrier

1. Solderable Surface Ti/Ni/Ag - Suffix "Ag" 2. Wire Bond Surface Aluminium - Suffix "Al"





Electrical Characteristics @ 25°c	Symbol	Unit	SB040P200-W-Ag/AI (See <u>ordering code</u> below)
Maximum Repetitive Reverse Voltage (2)	V <sub>RRM</sub>	Volt	200
Maximum Forward Voltage (1)(2)	V <sub>F</sub>	Volt	0.83
Typical Average Forward Rectified Current (2)	I <sub>F(AV)</sub>	Amp	1
Reverse Leakage Current (2)	I <sub>R</sub>	μA	10
Reverse Leakage Current @ 125°C (2)	I <sub>R</sub>	mA	5
Junction Operating Temperature Range (2)	TJ	°C	-65 to +150
Storage Temperature Range (2)	T <sub>SG</sub>	°C	-65 to +150

(1) Pulse Width tp = < 300µS, Duty Cycle <2%

(2) The characteristics above assume the die are assembled in indusry standard packages using appropriate attach methods.



